

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

Claims 1-8 (canceled).

Claim 9 (new): A semiconductor device comprising:

at least a first and a second power source system, the first and second power source systems each including:

a power supply bonding pad, a ground bonding pad, and at least one signal bonding pad arranged on a semiconductor substrate;

an I/O circuit that is connected to each of the power supply bonding pad, the ground bonding pad and the at least one signal bonding pad, and arranged to input or output a signal from or to the signal bonding pad; and

a first ESD protective bonding pad and a signal ESD protective element section connected to the signal bonding pad and the first ESD protective bonding pad; wherein

the first ESD protective bonding pads of the first and second power source systems are connected to one another.

Claim 10 (new): The semiconductor device according to claim 9, further comprising a power source ESD protective element section connected to either of the first ESD protective bonding pads of the first and second power source systems.

Claim 11 (new): The semiconductor device according to claim 9, wherein each of the first and second power source systems further comprises a power supply terminal connected to the power supply bonding pad, a ground terminal connected to the ground bonding pad, and a signal terminal connected to the signal bonding pad; wherein, in each of the first and second power source systems, the first ESD protective bonding pad is connected to one of the power supply terminal and the ground terminal.

Claim 12 (new): The semiconductor device according to claim 11, wherein, in each of the first and second power source systems, the connection between the power supply bonding pad and the power supply terminal, the connection between the ground bonding pad and the ground terminal, the connection between the signal bonding pad and the signal terminal, and the connection between the first ESD protective bonding pad and one of the power supply terminal and the ground terminal, are via bonding wire.

Claim 13 (new): The semiconductor device according to claim 9, wherein each of the first and second power source systems further comprises, on the semiconductor substrate, a second ESD protective bonding pad connected to the signal ESD protective

element section, and the second ESD protective bonding pads of the first and second power source systems are connected to one another.

Claim 14 (new): The semiconductor device according to claim 13, further comprising a power source ESD protective element section connected to either of the first ESD protective bonding pads and to either of the second ESD protective bonding pads of the first and second power source systems.

Claim 15 (new): The semiconductor device according to claim 14, wherein each of the first and second power source systems further comprises:

a power supply terminal connected to the power supply bonding pad, a ground terminal connected to the ground bonding pad, and a signal terminal connected to the signal bonding pad; wherein

in each of the first and second power source systems, the first ESD protective bonding pad is connected to one of the power supply terminal and the ground terminal, and the second ESD protective bonding pad is connected to the other of the power supply terminal and the ground terminal.

Claim 16 (new): The semiconductor device according to claim 15, wherein, in each of the first and second power source systems, the connection between the power supply bonding pad and the power supply terminal, the connection between the ground bonding pad and the ground terminal, the connection between the signal bonding pad

and the signal terminal, the connection between the first ESD protective bonding pad and one of the power supply terminal and the ground terminal, and the connection between the second ESD protective bonding pad and the other of the power supply terminal and the ground terminal, are via bonding wire.

Claim 17 (new): The semiconductor device according to claim 13, wherein each of the first and second power source systems further comprises:

a power supply terminal connected to the power supply bonding pad, a ground terminal connected to the ground bonding pad, and a signal terminal connected to the signal bonding pad; wherein

in each of the first and second power source systems, the first ESD protective bonding pad is connected to one of the power supply terminal and the ground terminal, and the second ESD protective bonding pad is connected to the other of the power supply terminal and the ground terminal.

Claim 18 (new): The semiconductor device according to claim 17, wherein, in each of the first and second power source systems, the connection between the power supply bonding pad and the power supply terminal, the connection between the ground bonding pad and the ground terminal, the connection between the signal bonding pad and the signal terminal, the connection between the first ESD protective bonding pad and one of the power supply terminal and the ground terminal, and the connection

between the second ESD protective bonding pad and the other of the power supply terminal and the ground terminal, are via bonding wire.

Claim 19 (new): The semiconductor device according to claim 10, wherein each of the first and second power source systems further comprises a power supply terminal connected to the power supply bonding pad, a ground terminal connected to the ground bonding pad, and a signal terminal connected to the signal bonding pad; wherein, in each of the first and second power source systems, the first ESD protective bonding pad is connected to one of the power supply terminal and the ground terminal.

Claim 20 (new): The semiconductor device according to claim 19, wherein, in each of the first and second power source systems, the connection between the power supply bonding pad and the power supply terminal, the connection between the ground bonding pad and the ground terminal, the connection between the signal bonding pad and the signal terminal, and the connection between the first ESD protective bonding pad and one of the power supply terminal and the ground terminal, are via bonding wire.